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cont.*
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2. (Amended) The semiconductor device according to claim 1, wherein the crystalline film, when subjected to X-ray diffraction, has a spectrum having a first peak between 36 degrees and 38 degrees and a second peak between 42 degrees and 44 degrees.
3. (Amended) The semiconductor device of claim 2, wherein a half-width of the first peak is 3.2 degrees or less.
4. (Amended) The semiconductor device of claim 2, wherein a half-width of the second peak is 2.6 degrees or less.
5. (Amended) A semiconductor device comprising:  
an insulator film formed on a substrate;  
a wiring layer of copper formed on the insulator film; and  
a crystalline film for preventing copper diffusion from the wiring layer to the insulator film, the crystalline film formed of a material comprising tungsten, carbon, and nitrogen, the crystalline film arranged between the insulator film and the wiring layer.

- A<sup>4</sup>*
14. (New) A semiconductor device comprising:  
an insulator film formed on a substrate;  
a crystalline film formed on the insulator; and  
a wiring layer of copper formed on the crystalline film,  
wherein the crystalline film prevents copper diffusion from the wiring layer to the insulator film.

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15. (New) The semiconductor device according to claim 14, wherein the crystalline film comprises WC<sub>x</sub>N<sub>y</sub>.

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16. (New) The semiconductor device according to claim 14, wherein the crystalline film, when subjected to X-ray diffraction, has a spectrum having a first peak between 36 degrees and 38 degrees and a second peak between 42 degrees and 44 degrees.
  17. (New) The semiconductor device according to claim 16, wherein a half-width of the first peak is 3.2 degrees or less.
  18. (New) The semiconductor device according to claim 16, wherein a half-width of the second peak is 2.6 degrees or less.

#### REMARKS

In the Office Action dated January 15, 2002, the Examiner acknowledges the claim for foreign priority under 35 U.S.C. § 119(a)-(d) and 365(c) and the receipt of certified copies of the priority documents. However, the Examiner fails to acknowledge, in item 15 of the Office Action Summary, a claim for domestic priority under 35 U.S.C. § 120. Thus, Applicant respectfully requests the Examiner to acknowledge the claim for domestic priority under 35 U.S.C. § 120 in the next communication.

In the outstanding Office Action, the Examiner: objected to drawings; objected to specification; rejected claims 1 and 5 under 35 U.S.C. § 102(b) as being anticipated by Ueno (JP 10-209073); rejected claims 1 and 5 under 35 U.S.C. § 102(e) as being anticipated by Vitkavage et al. (U.S. Patent No. 5,858,873); rejected claims 2-4 under 35 U.S.C. § 103(a) as being unpatentable over Ueno (JP 10-209073); and rejected claims 2-4 under 35 U.S.C. § 103(a) as being unpatentable over in view of Vitkavage et al. (U.S. Patent No. 5,858,873).

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